CY62138CV25/30/33 MoBL®
CY62138CV MoBL®

2M (256K x 8) Static RAM

Features

- **Very High Speed: 55 ns and 70 ns**
- **Voltage range:**
  - **CY62138CV25: 2.2V–2.7V**
  - **CY62138CV30: 2.7V–3.3V**
  - **CY62138CV33: 3.0V–3.6V**
  - **CY62138CV: 2.7V–3.6V**
- **Pin compatible with CY62138V**
- **Ultra low active power**
  - **Typical active current: 1.5 mA @ f = 1 MHz**
  - **Typical active current: 7 mA @ f = f_{max} (70 ns speed)**
- **Low standby power**
- **Easy memory expansion with $\overline{CE}_1$, CE_2, and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Packages offered in a 36-ball FBGA**

Functional Description[1]

The CY62138CV25/30/33 and CY62138CV are high-performance CMOS static RAMs organized as 256K words by 8 bits.

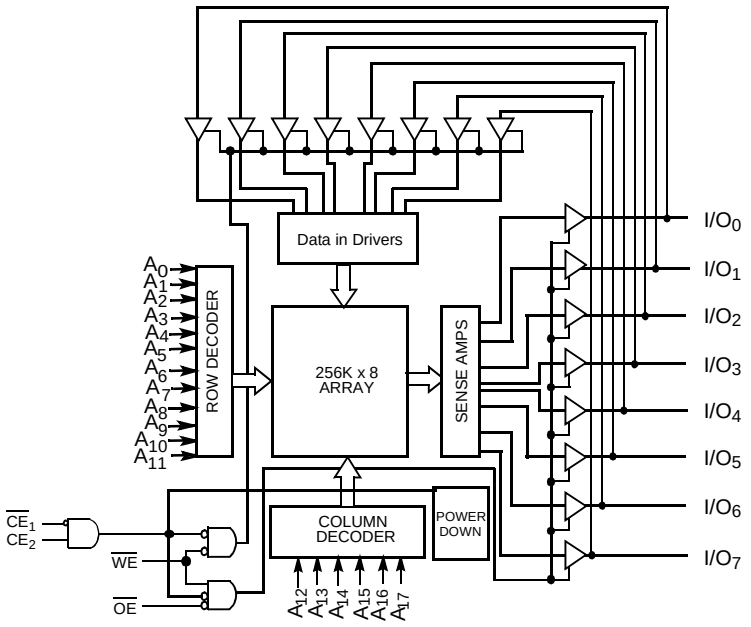
This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications. The device also has an automatic power-down feature that significantly reduces power consumption by 80% when addresses are not toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{CE}_1$ HIGH or CE_2 LOW).

Writing to the device is accomplished by taking Chip Enable 1 ($\overline{CE}_1$) and Write Enable ($\overline{WE}$) inputs LOW and Chip Enable 2 (CE_2) HIGH. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable 1 ($\overline{CE}_1$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) and Chip Enable 2 (CE_2) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

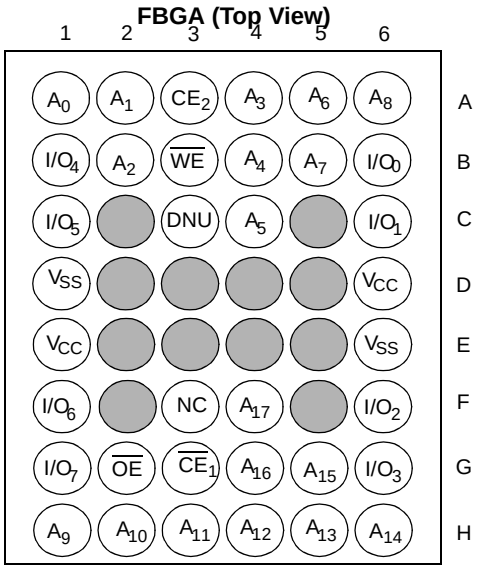
The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected ($\overline{CE}_1$ HIGH or CE_2 LOW), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}_1$ LOW, CE_2 HIGH and $\overline{WE}$ LOW). See the truth table at the back of this data sheet for a complete description of read and write modes.

Logic Block Diagram



Note:
1. For best practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration [2, 3]



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ... .–65°C to +150°C

Ambient Temperature with Power Applied... .....55°C to +125°C

Supply Voltage to Ground Potential.....–0.5V to V_{ccmax} + 0.5V

DC Voltage Applied to Outputs in High Z State[4].....0.5V to V_{CC} + 0.5V

DC Input Voltage[4].....–0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW) .....20 mA

Static Discharge Voltage.. .....>2001V (per MIL-STD-883, Method 3015)

Latch-Up Current.....>200 mA

Operating Range

Product	Range	Ambient Temperature T_A	V_{CC}
CY62138CV25	Industrial	–40°C to +85°C	2.2V to 2.7V
CY62138CV30			2.7V to 3.3V
CY62138CV33			3.0V to 3.6V
CY62138CV			2.7V to 3.6V

Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating, I_{CC} (mA)				Standby, I_{SB2} (µA)	
					f = 1 MHz		f = f_{max}			
	Min.	Typ.[5]	Max.		Typ.[5]	Max.	Typ.[5]	Max.	Typ.[5]	Max.
CY62138CV25LL	2.2	2.5	2.7	55	1.5	3	12	25	2	10
				70	1.5	3	7	15		
CY62138CV30LL	2.7	3.0	3.3	55	1.5	3	12	25	2	10
				70	1.5	3	7	15		
CY62138CV33LL	3.0	3.3	3.6	55	1.5	3	12	25	5	15
				70	1.5	3	7	15		
CY62138CVLL	2.7	3.3	3.6	70	1.5	3	7	15	5	15

Notes:
2. NC Pins are not connected to the die.
3. C3 (DNU) can be left as NC or V_{SS} to ensure proper application.
4. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
5. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ.)}$, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62138CV25-55 Min.	CY62138CV25-55 Typ.[5]	CY62138CV25-55 Max.	CY62138CV25-70 Min.	CY62138CV25-70 Typ.[5]	CY62138CV25-70 Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 2.2V	2.0			2.0			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 2.2V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			1.8		V_{CC}+ 0.3V	1.8		V_{CC}+ 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.6	–0.3		0.6	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = 2.7V, I_{OUT} = 0 mA CMOS Levels		12	25		7	15	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f = 0 ($\overline{OE}$,$\overline{WE}$)			2	10		2	10	µA
I_{SB2}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 2.7V								

Parameter	Description	Test Conditions		CY62138CV30-55 Min.	CY62138CV30-55 Typ.[5]	CY62138CV30-55 Max.	CY62138CV30-70 Min.	CY62138CV30-70 Typ.[5]	CY62138CV30-70 Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.7V	2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 2.7V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.2		V_{CC}+ 0.3V	2.2		V_{CC}+ 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.8	–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	V_{CC} = 3.3V, I_{OUT} = 0 mA CMOS Levels		12	25		7	15	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f = 0 ($\overline{OE}$,$\overline{WE}$)			2	10		2	10	µA
I_{SB2}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC}=3.3V								

Electrical Characteristics Over the Operating Range (continued)

Parameter	Description	Test Conditions		CY62138CV33-55			CY62138CV33-70 CY62138CV-70			Unit
				Min.	Typ.[5]	Max.	Min.	Typ.[5]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 3.0V	2.4			2.4			V
			V_{CC} = 2.7V				2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 3.0V			0.4			0.4	V
			V_{CC} = 2.7V						0.4	V
V_{IH}	Input HIGH Voltage			2.2		V_{CC}+ 0.3V	2.2		V_{CC}+ 0.3V	V
V_{IL}	Input LOW Voltage			–0.3		0.8	–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = 3.6V I_{OUT} = 0 mA CMOS Levels		12	25		7	15	mA
		f = 1 MHz			1.5	3		1.5	3	
I_{SB1}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = f_{max} (Address and Data Only), f = 0 ($\overline{OE}$,$\overline{WE}$)			5	15		5	15	µA
I_{SB2}	Automatic CE Power-Down Current— CMOS Inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.6V								

Capacitance[6]

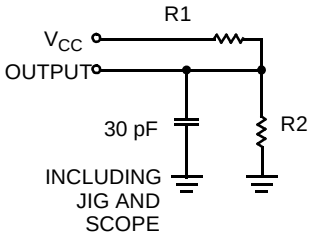
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ.)}$	6	pF
C_{OUT}	Output Capacitance		8	pF

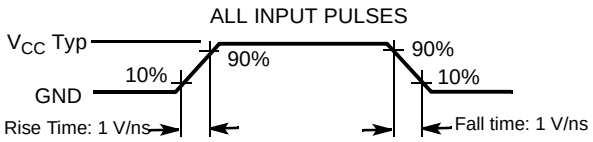
Thermal Resistance

Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance[6] (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, two-layer printed circuit board	Θ_{JA}	55	°C/W
Thermal Resistance[6] (Junction to Case)		Θ_{JC}	16	°C/W

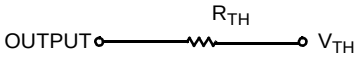
Note:
6. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms





Equivalent to: THÉVENIN EQUIVALENT

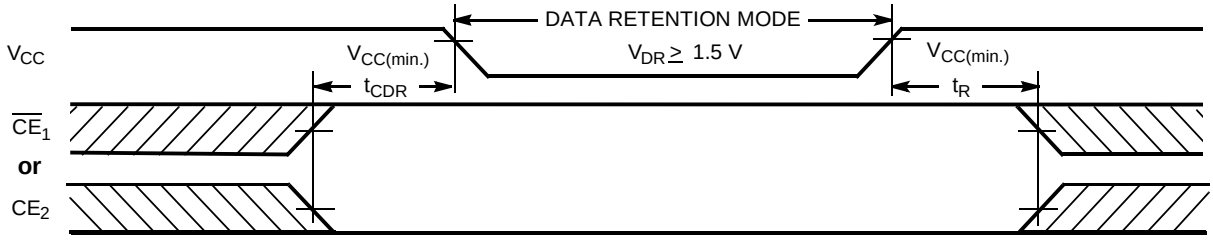


Parameters	2.5V	3.0V	3.3V	Unit
R1	16600	1105	1216	Ω
R2	15400	1550	1374	Ω
R_{TH}	8000	645	645	Ω
V_{TH}	1.20	1.75	1.75	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[5]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1.5		$V_{CC(max.)}$	V
I_{CCDR}	Data Retention Current	V_{CC} = 1.5V $\overline{CE}_1 \geq V_{CC} - 0.2V$ or $CE_2 \leq 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		1	6	µA
t_{CDR}[6]	Chip Deselect to Data Retention Time		0			ns
t_R[7]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform



Note:
7. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 100$ µs or stable at $V_{CC(min.)} \geq 100$ µs.

Switching Characteristics Over the Operating Range[8]

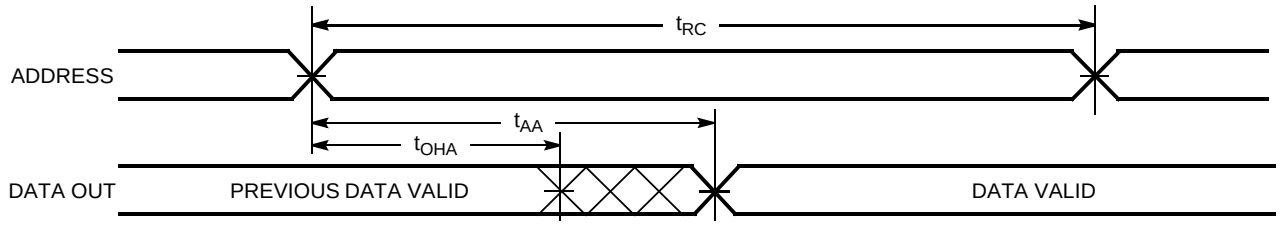
Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[9]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[9, 10]		20		25	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Low Z[9]	10		10		ns
t_{HZCE}	$\overline{CE}_1$ HIGH or CE_2 LOW to High Z[9, 10]		20		25	ns
t_{PU}	$\overline{CE}_1$ LOW and CE_2 HIGH to Power-Up	0		0		ns
t_{PD}	$\overline{CE}_1$ HIGH or CE_2 LOW to Power-Down		55		70	ns
Write Cycle[11]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Write End	45		60		ns
t_{AW}	Address Set-Up to Write End	45		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		45		ns
t_{SD}	Data Set-Up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[9, 10]		20		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[9]	5		10		ns

Notes:

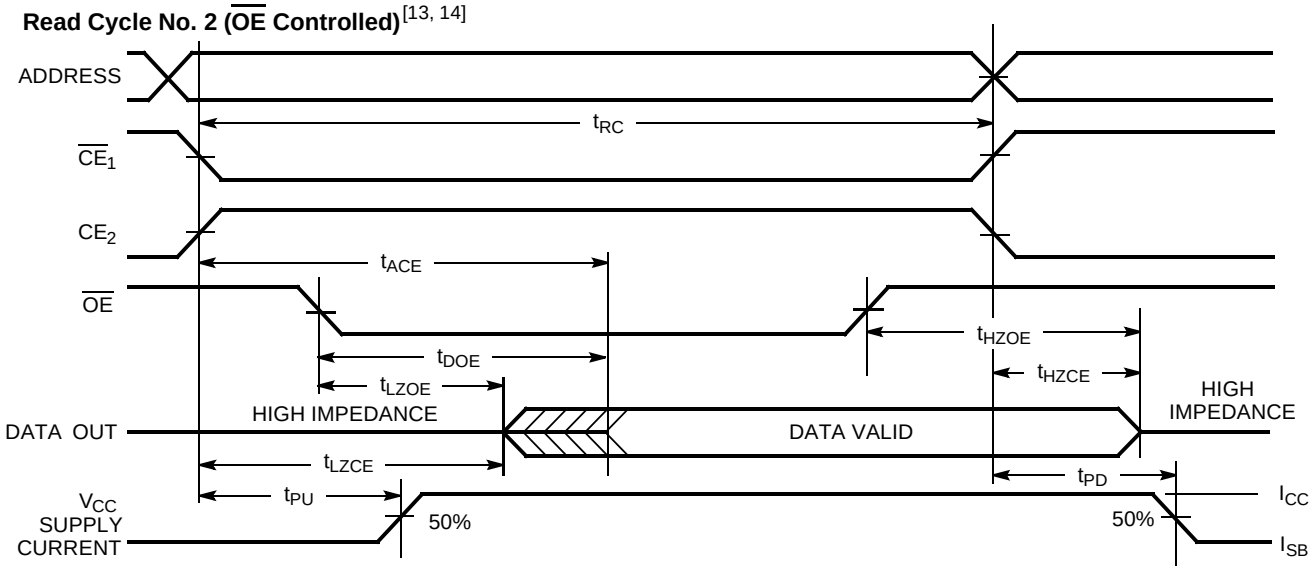
8. Test conditions assume signal transition time of 5 ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
10. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
11. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}_1 = V_{IL}$, and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle No. 1 (Address Transition Controlled) [12, 13]



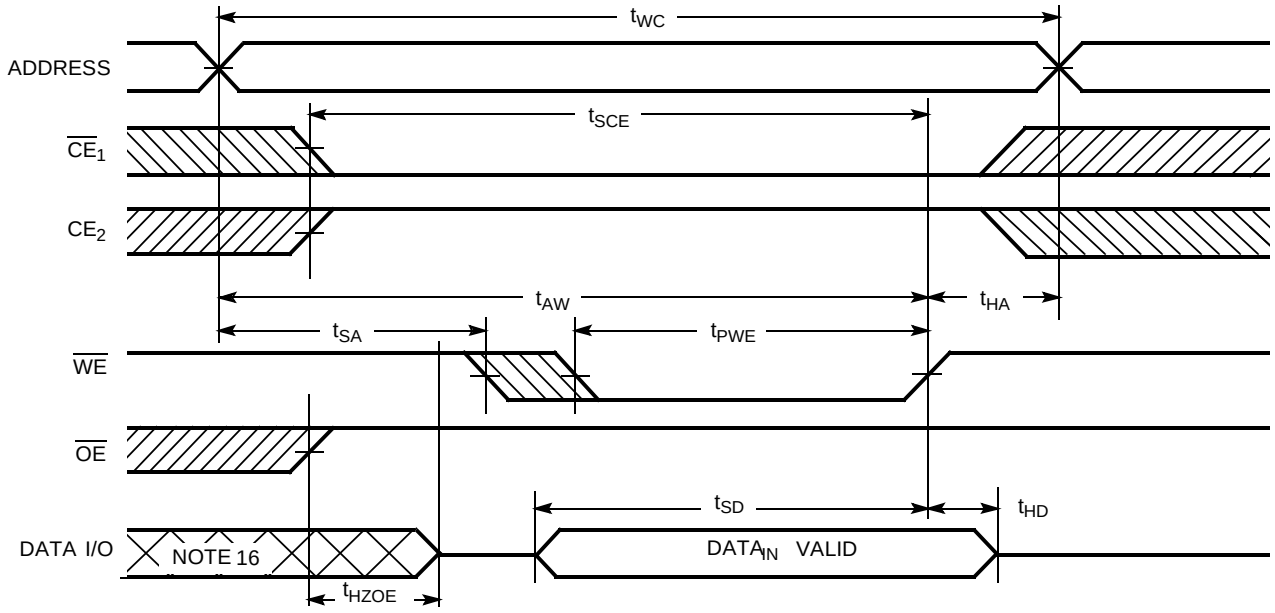
Read Cycle No. 2 ($\overline{OE}$ Controlled) [13, 14]



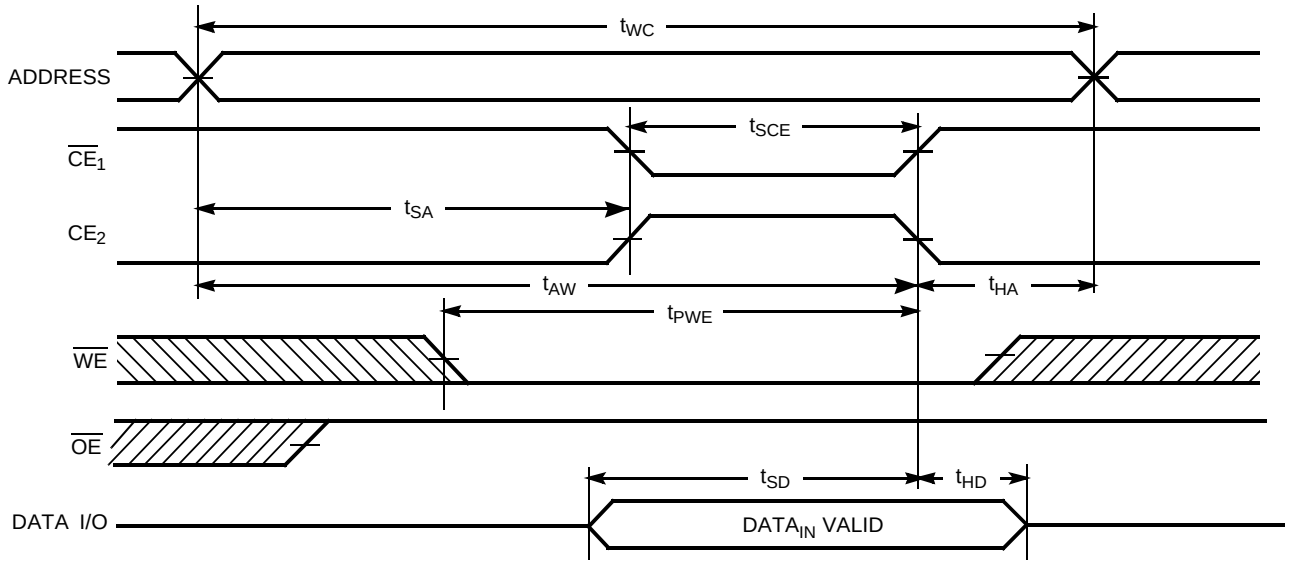
Notes:
12. Device is continuously selected. $\overline{OE}$, $\overline{CE}_1$ = V_{IL}, CE_2=V_{IH}.
13. $\overline{WE}$ is HIGH for read cycle.
14. Address valid prior to or coincident with $\overline{CE}_1$ transition LOW and CE_2 transition HIGH.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{WE}$ Controlled)[11, 15, 17]



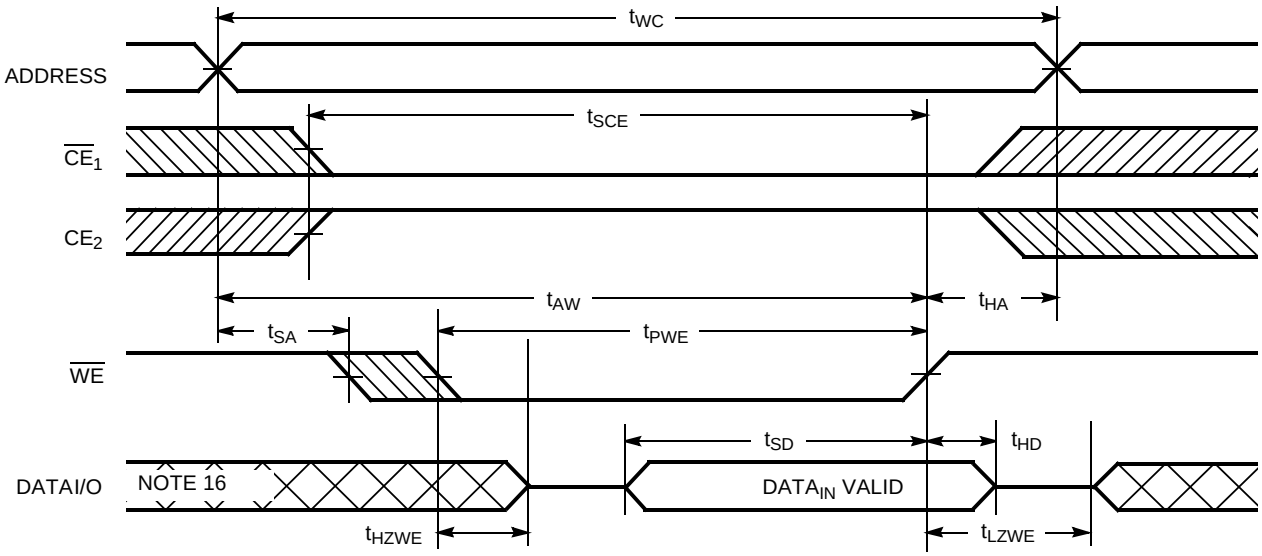
Write Cycle No. 2 ($\overline{CE_1}$ or CE_2 Controlled)[11, 15, 17]



Notes:
15. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
16. During this period, the I/Os are in output state and input signals should not be applied.
17. If $\overline{CE_1}$ goes HIGH or CE_2 goes LOW simultaneously with $\overline{WE}$ HIGH, the output remains in high-impedance state.

Switching Waveforms (continued)

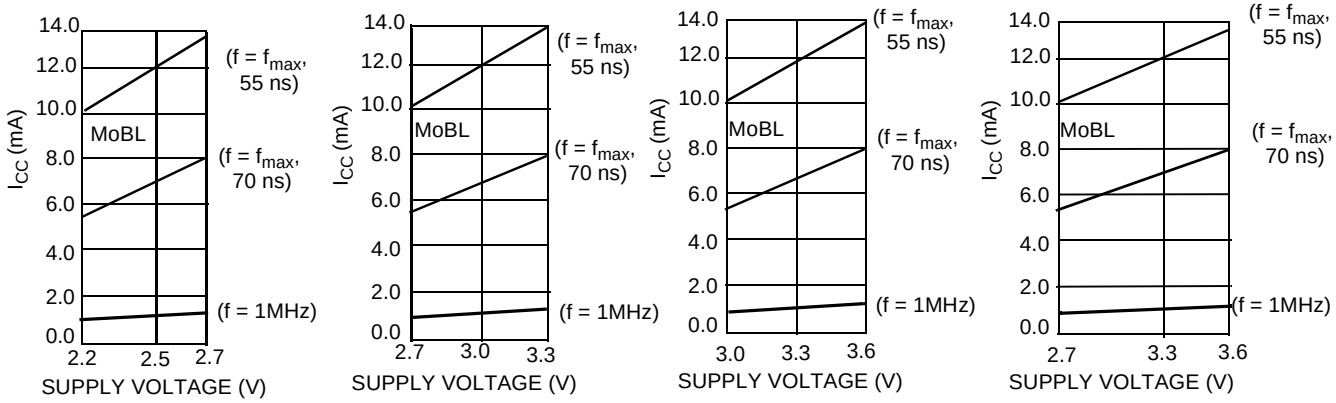
Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) [17]



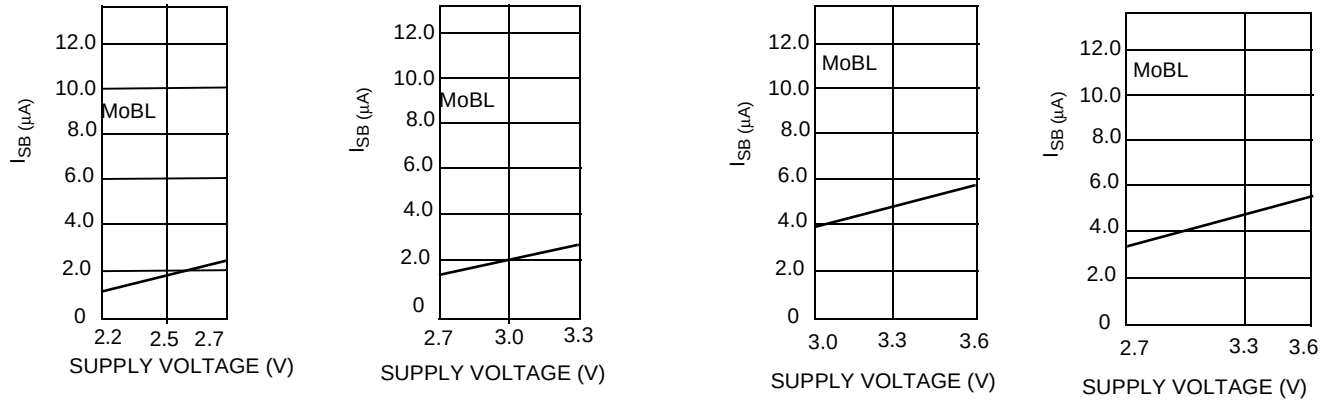
Typical DC and AC Parameters

(Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$)

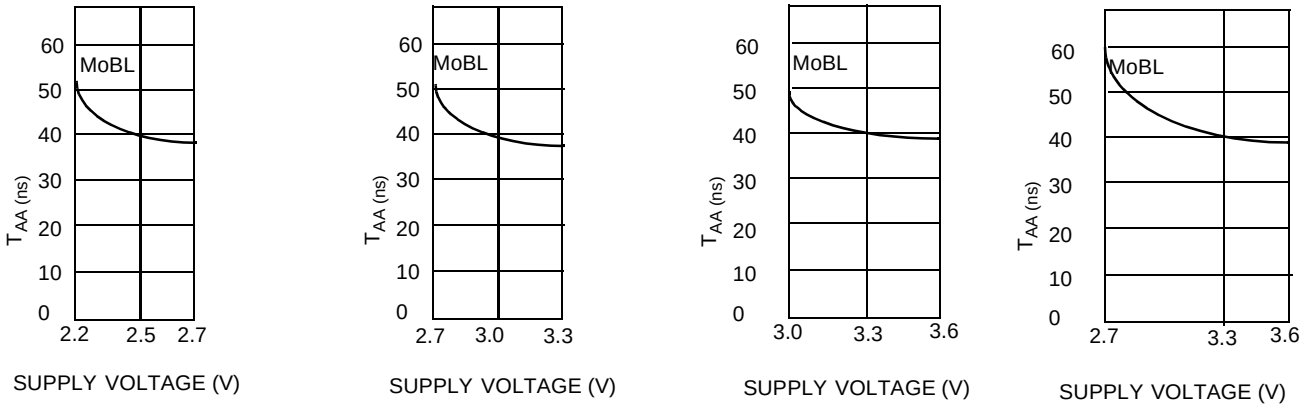
Operating Current vs. Supply Voltage



Standby Current vs. Supply Voltage



Access Time vs. Supply Voltage



Truth Table

$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
X	L	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	H	L	Data Out (I/O_0-I/O_7)	Read	Active (I_{CC})
L	H	H	H	High Z	Output Disabled	Active (Icc)

Truth Table

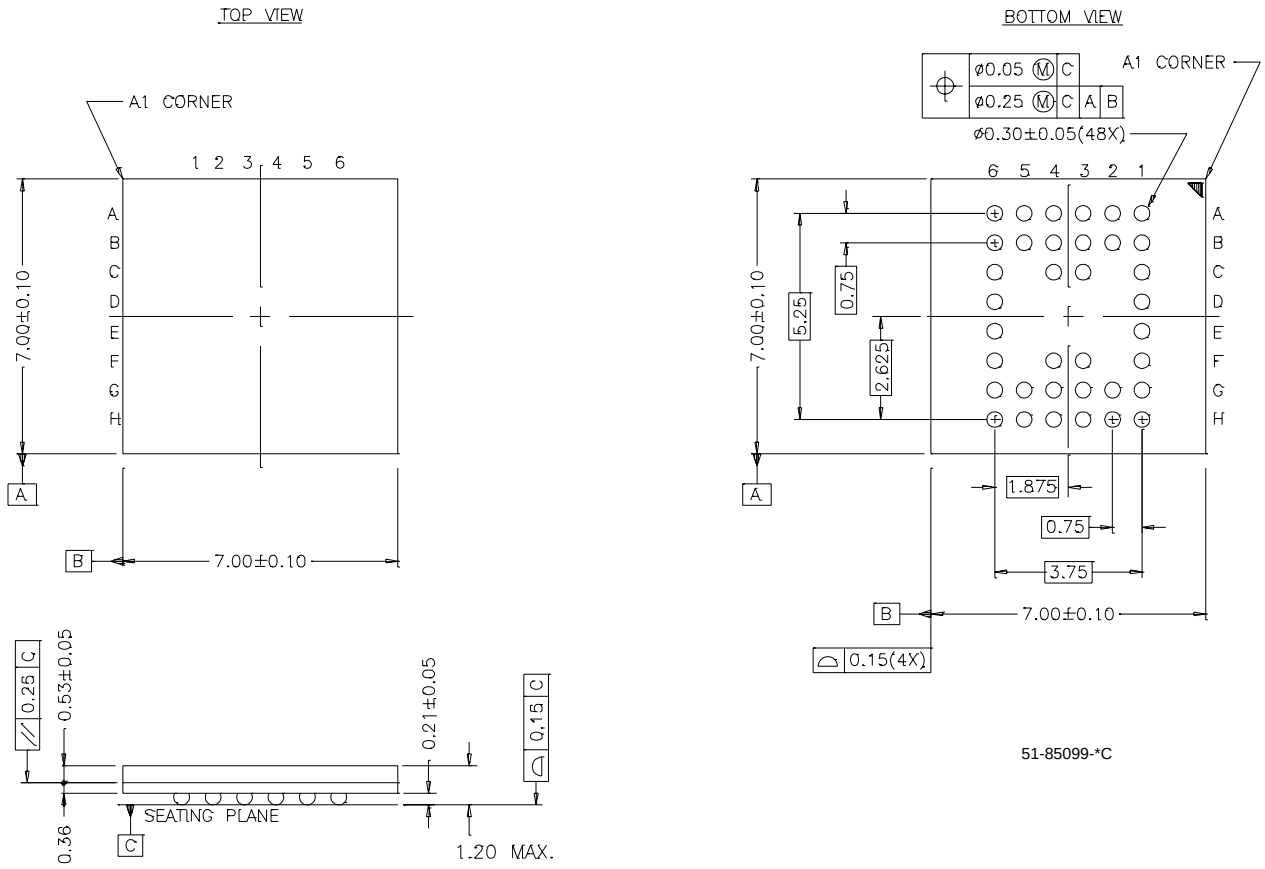
$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
L	H	L	X	Data in (I/O_0-I/O_7)	Write	Active (Icc)

Ordering Information

Speed (ns)	Ordering Code	Voltage Range (V)	Package Name	Package Type	Operating Range
70	CY62138CV25LL-70BAI	2.2–2.7	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	Industrial
	CY62138CV25LL-70BVI	2.2–2.7	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62138CV30LL-70BAI	2.7–3.3	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CV30LL-70BVI	2.7–3.3	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62138CV33LL-70BAI	3.0–3.6	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CV33LL-70BVI	3.0–3.6	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62138CVLL-70BAI	2.7–3.6	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CVLL-70BVI	2.7–3.6	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
55	CY62138CV25LL-55BAI	2.2–2.7	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CV25LL-55BVI	2.2–2.7	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62138CV30LL-55BAI	2.7–3.3	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CV30LL-55BVI	2.7–3.3	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62138CV33LL-55BAI	3.0–3.6	BA36A	36-Ball Fine Pitch BGA (7 mm x 7 mm x 1.2mm)	
	CY62138CV33LL-55BVI	3.0–3.6	BV36A	36-Ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	

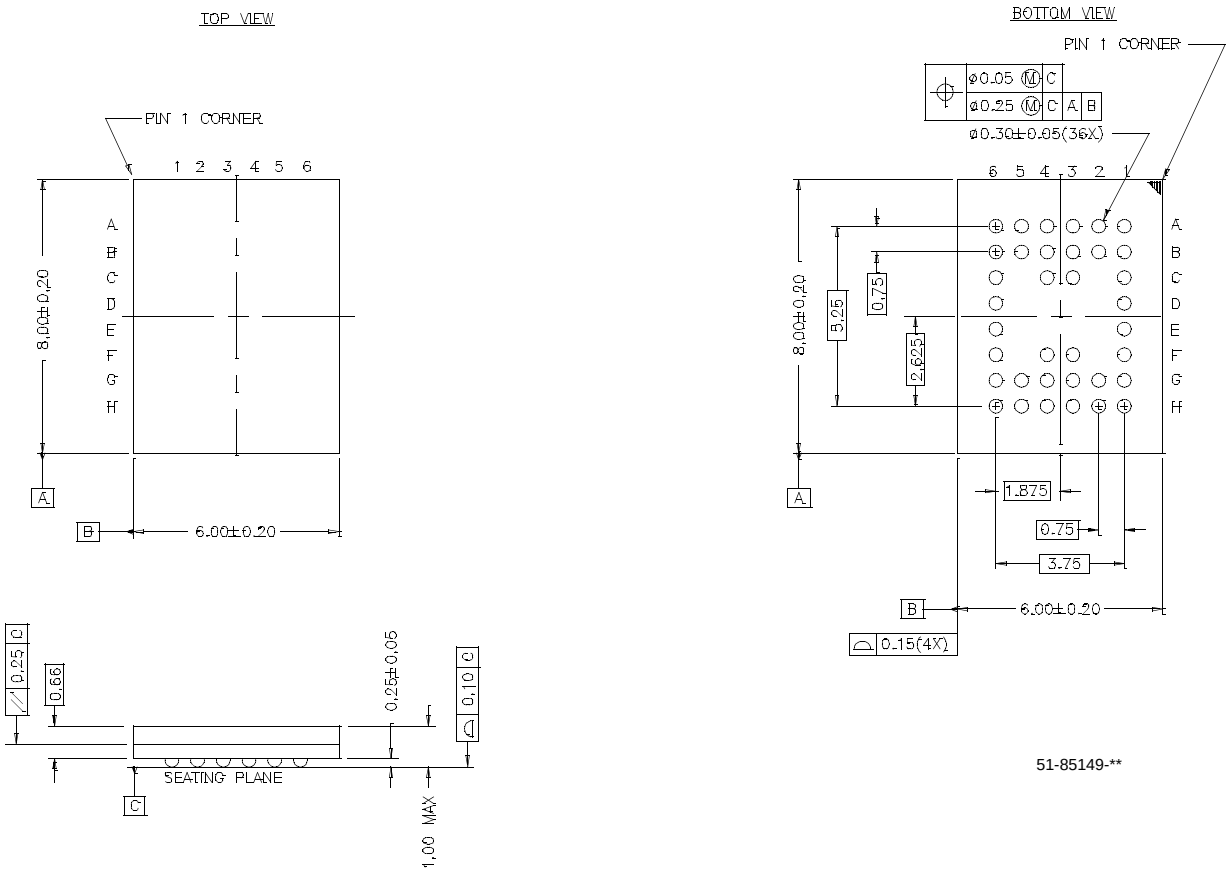
Package Diagrams

36-Ball FBGA (7 x 7 x 1.2 mm) BA36A



Package Diagrams (continued)

36-Lead VFBGA (6.0 mm x 8.0 mm x 1.0 mm) BV36A



Document Title: CY62138CV25/30/33 MoBL® and CY62138CV MoBL® 2M (256K x 8) Static RAM Document Number: 38-05200				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	112381	02/19/02	GAV	New Data Sheet-Advance Information
*A	114024	04/25/02	JUI	Add BV package diagram. Change from Advance Information to Preliminary.
*B	117062	07/12/02	MGN	Add Second Chip Enable. Change from Preliminary to Final.
*C	118123	09/09/02	MGN	Add new part number - CY62138CV with wider voltage (2.7V - 3.6V). For T_{AA} = 55 ns, improved t_{PWE} Min from 45 ns to 40 ns. For T_{AA} = 70 ns, improved t_{PWE} Min from 60 ns to 45 ns. For T_{AA} = 70 ns, improved t_{LZWE} Min from 5 ns to 10 ns.